

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9558	(438/634 or 438/637 or 438/649 or 438/655 or 438/656 or 438/667 or 438/668 or 438/672 or 438/675 or 438/709 or 438/710 or 438/712).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:29
L2	8590	(microloading near effect) or over-etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:29
L3	208644	(contact near hole\$1) or (contact near plug\$1) or through-hole\$1 or viahole\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:30
L4	48632	etch\$3 near3 rat\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:31
L5	604317	(insulat\$3 near (layer or film)) or (dielectric near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:32
L6	241442	FET or MOSFET or (field near effect near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:32
L7	379	I2 and I3 and I4 and I5 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:33
L8	883	I1 and I3 and I4 and I5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/09 09:34